

RB717F SCHOTTKY BARRIER DIODE

FEATURES:

Power dissipation

$$P_D: 200 \text{ mW (T}_{amb}=25^{\circ}\text{C)}$$

Collector current

$$I_F: 30 \text{ mA}$$

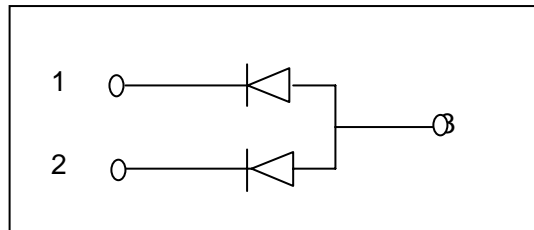
Collector-base voltage

$$V_R: 40 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^{\circ}\text{C to } +150^{\circ}\text{C}$$

CIRCUIT:



MARKING: 3E

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	40		V
Reverse voltage leakage current	I_R	$V_R=10\text{V}$		1	μA
Forward voltage	V_F	$I_F=1\text{mA}$		0.37	V
Diode capacitance	C_D	$V_R=1\text{V}, f=1\text{MHz}$		5	pF

